SIDE-LOOK PACKAGE
PIN PHOTODIODE

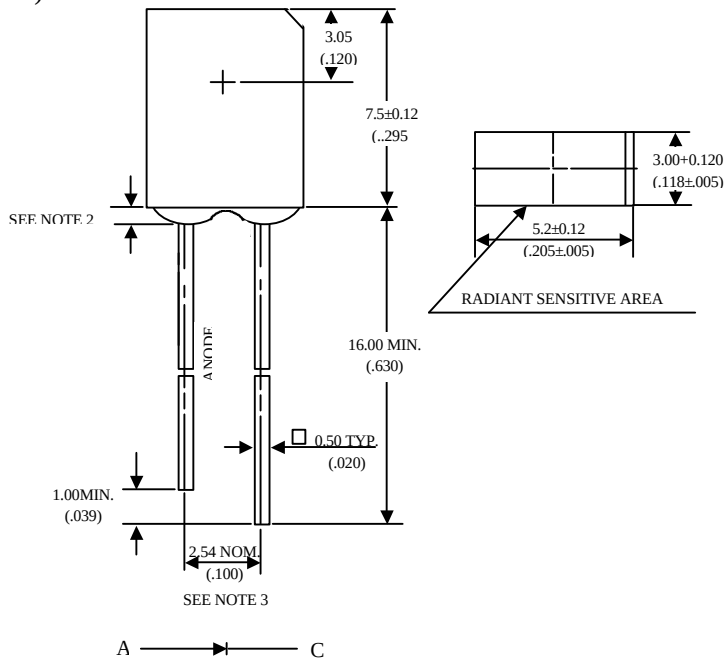
MID-73H1C

Description

The MID-73H1C is a photodiode mounted in special dark plastic package and suitable for the IRED (850nm / 880nm) Type.

Package Dimensions

Unit : mm (inches)



Features

- High photo sensitivity
- Low junction capacitance
- High cut-off frequency
- Fast switching time

Notes :
1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.0 mm (.040") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ T_A=25°C

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	I_R=0.1mA Ee=0	$V_{(BR)R}$	30			V
Reverse Dark Current	V_R=10V Ee=0	I_D			30	nA
Open Circuit Voltage	λ=850nm Ee=0.1mW/cm^2	V_{OC}		350		mV
Rise Time	V_R =10V λ=850nm	Tr		50		nsec
Fall Time	R_L=50Ω	Tf		50		
Light Current	V_R =5V, λ=850nm Ee=0.1mW/cm^2	I_L		9		μA
Total Capacitance	V_R =3V, f=1MHz Ee=0	C_T		25		pF

Typical Optical-Electrical Characteristic Curves

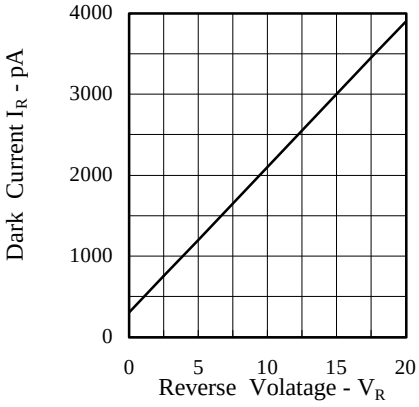


FIG.1 DARK CURRENT VS REVERSE VOLTAGE
TEMP=25°C , Ee=0 mW/cm^2

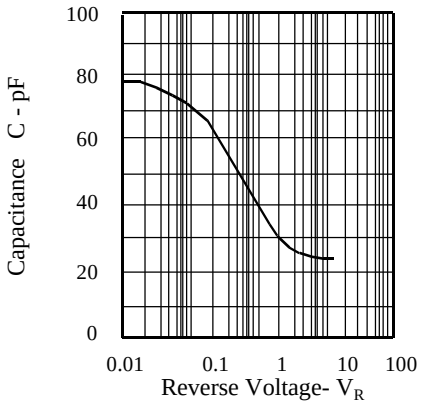


FIG.2 CAPACITANCE VS. REVERSE VOLTAGE
F=1MHZ, Ee=0mW/cm^2

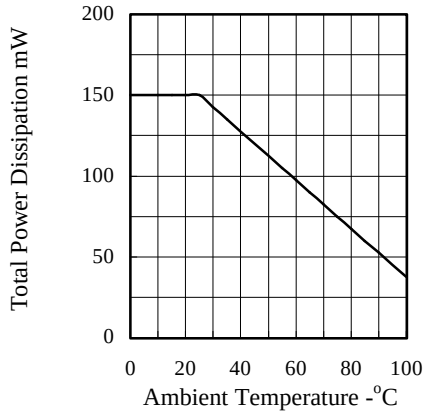


FIG.3 TOTAL POWER DISSIPATION
VS. AMBIENT TEMPERATURE

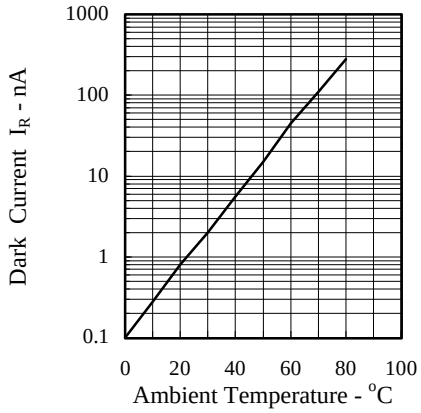


FIG.4 DARK CURRENT VS AMBIENT TEMPERATURE
V_R=10, Ee=0 mw/cm^2

Typical Optical-Electrical Characteristic Curves

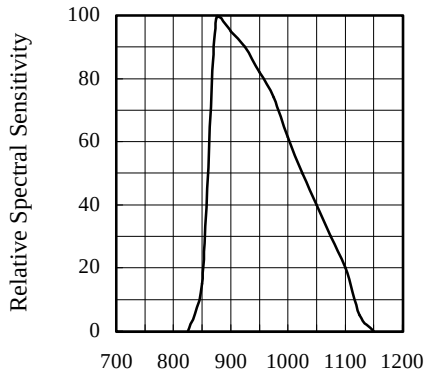


FIG.5 RELATIVE SPECTRAL SENSITIVITY VS. WAVELENGTH

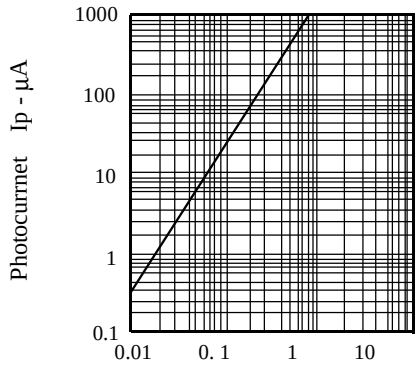


FIG.6 PHOTOCURRENT VS. IRRADIANCE = 850 nm

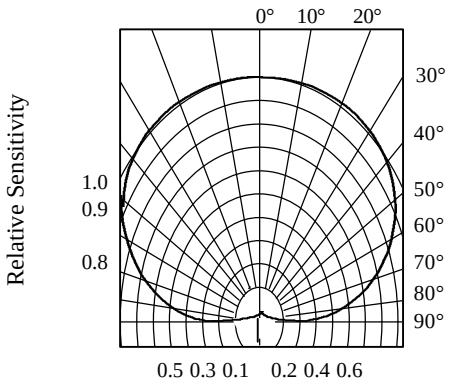


FIG.7 SENSITIVITY DIAGRAM